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Manufacturers of World Class Discrete Semiconductors

2N6732

PNP SILICON TRANSISTOR

JEDEC TO-237 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6732 is a PNP silicon plastic power transistor designed for general purpose power amplifier and switching applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EB0}	5.0	V
Collector Current	I _C	1.0	A
Base Current	I _B	0.5	W
Power Dissipation	P _D	1.0	W
Power Dissipation (T _C =25°C)	P _D	2.0	
Operating and Storage		.	
Junction Temperature	T _J , T _{STG}	-65 to +150	°C
Thermal Resistance	θ _{JA}	125	°C/W
Thermal Resistance	θ _{JC}	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CB0}	V _{CB} =80V		0.1	μA
I _{EB0}	V _{EB} =5.0V		10	μA
BV _{CB0}	I _C =0.1mA	100		V
BV _{CEO}	I _C =10mA	80		V
BV _{EB0}	I _E =1.0mA	5.0		V
V _{CE(SAT)}	I _C =350mA, I _B =35mA		0.35	V
V _{BE(ON)}	V _{CE} =2.0V, I _C =350mA		1.0	V
h _{FE}	V _{CE} =2.0V, I _C =10mA	100	-	
h _{FE}	V _{CE} =2.0V, I _C =350mA	100	300	
f _T	V _{CE} =5.0V, I _C =200mA, f=20MHz	50	500	MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		20	pF

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Datasheets for electronics components.